ON Semiconductor

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JFETs - General Purpose

N-Channel – Depletion

N-Channel Junction Field Effect Transistors, depletion mode (Type A) designed for audio and switching applications.

Features

- N-Channel for Higher Gain
- Drain and Source Interchangeable
- High AC Input Impedance
- High DC Input Resistance
- Low Transfer and Input Capacitance
- Low Cross-Modulation and Intermodulation Distortion
- Plastic Encapsulated Package
- Pb-Free Packages are Available*

MAXIMUM RATINGS

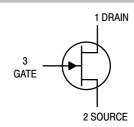
Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	25	Vdc
Drain-Gate Voltage	V _{DG}	25	Vdc
Reverse Gate – Source Voltage	V _{GSR}	-25	Vdc
Gate Current	l _G	10	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	310 2.82	mW mW/°C
Operating Junction Temperature	ТJ	135	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

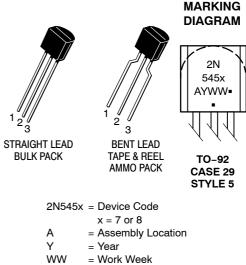
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
	·	
2N5457	TO-92	1000 Units/Box
2N5457G	TO-92 (Pb-Free)	1000 Units/Box
2N5458	TO-92	1000 Units/Box
2N5458G	TO-92 (Pb-Free)	1000 Units/Box

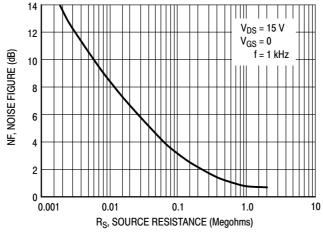
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						•
Gate – Source Breakdown Voltage $(I_G = -10 \ \mu Adc, V_{DS} = 0)$		V _{(BR)GSS}	-25	_	_	Vdc
$ \begin{array}{l} \mbox{Gate Reverse Current} \\ (V_{GS} = -15 \mbox{ Vdc}, V_{DS} = 0) \\ (V_{GS} = -15 \mbox{ Vdc}, V_{DS} = 0, \mbox{ T}_A = 100^{\circ}\mbox{C}) \end{array} $		I _{GSS}			- 1.0 -200	nAdc
Gate-Source Cutoff Voltage (V _{DS} = 15 Vdc, i _D = 10 nAdc)	2N5457 2N5458	V _{GS(off)}	-0.5 -1.0		-6.0 -7.0	Vdc
$\begin{array}{l} \mbox{Gate-Source Voltage} \\ (V_{DS} = 15 \mbox{ Vdc}, i_D = 100 \mu\mbox{Adc}) \\ (V_{DS} = 15 \mbox{ Vdc}, i_D = 200 \mu\mbox{Adc}) \end{array}$	2N5457 2N5458	V _{GS}		-2.5 -3.5		Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current (Note 1) $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0)$	2N5457 2N5458	I _{DSS}	1.0 2.0	3.0 6.0	5.0 9.0	mAdc
DYNAMIC CHARACTERISTICS						
Forward Transfer Admittance (Note 1) $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ kHz})$	2N5457 2N5458	Y _{fs}	1000 1500	3000 4000	5000 5500	μmhos
Output Admittance Common Source (Note 1) $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ kHz})$		Y _{os}	_	10	50	μmhos
Input Capacitance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1 kHz)		C _{iss}	_	4.5	7.0	pF
Reverse Transfer Capacitance $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1 \text{ kHz})$		C _{rss}	_	1.5	3.0	pF
Dulas Width < 620 ma. Duty Ovala < 10%						

1. Pulse Width \leq 630 ms, Duty Cycle \leq 10%.







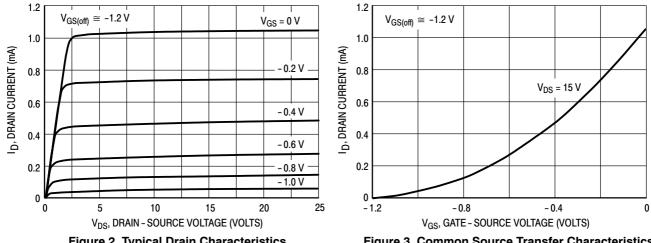
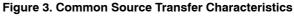
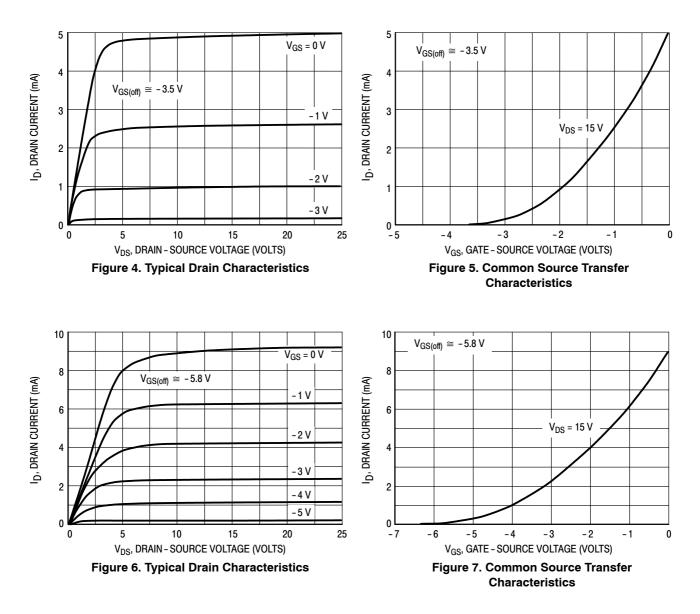


Figure 2. Typical Drain Characteristics



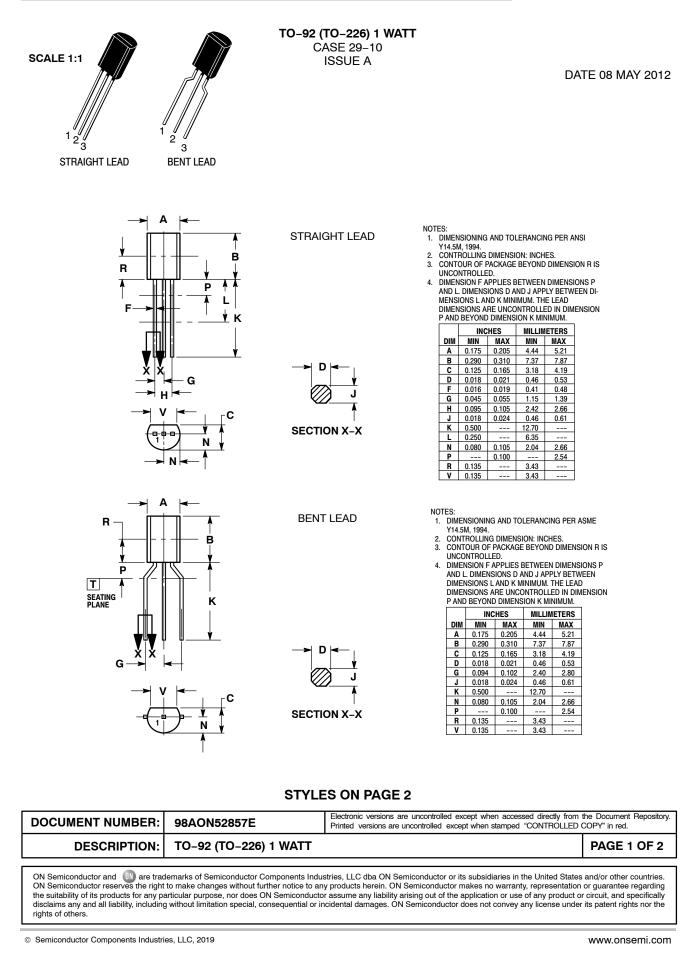
TYPICAL CHARACTERISTICS For 2N5457 Only



NOTE: Note: Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher I_{DSS} units reduces I_{DSS}.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE A

DATE 08 MAY 2012

	EMITTER BASE COLLECTOR								
	GATE SOURCE & SUBSTRATE DRAIN								
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 Gate Main Terminal 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1 CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
STYLE 21: PIN 1. 2. 3.	COLLECTOR EMITTER BASE	STYLE 22: PIN 1. 2. 3.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	Emitter Collector/Anode Cathode	STYLE 25: PIN 1. 2. 3.	MT 1 GATE MT 2
STYLE 26: PIN 1. 2. 3.	V _{CC} GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	STYLE 28: PIN 1. 2. 3.	CATHODE ANODE GATE	STYLE 29: PIN 1. 2. 3.	NOT CONNECTED ANODE CATHODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE SOURCE
STYLE 31: PIN 1. 2. 3.	GATE DRAIN SOURCE	STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN INPUT OUTPUT	STYLE 34: PIN 1. 2. 3.	input Ground Logic	STYLE 35: PIN 1. 2. 3.	GATE COLLECTOR EMITTER

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